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(72) Inventors; and

(75) Inventors/Applicants (for US only): **SMYTHE III, John, A.** [US/US]; 4546 S Riva Ridge Way, Boise, ID 83709 (US). **SANDHU, Gurtej, S.** [US/US]; 2964 E Parkriver Drive, Boise, ID 83706 (US).(74) Agents: **KERN, Jacob T.** et al.; Brooks, Cameron & Huebsch, PLLC, 1221 Nicollet Avenue, Suite 500, Minneapolis, MN 55403 (US).

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(54) Title: GCIB-TREATED RESISTIVE DEVICE

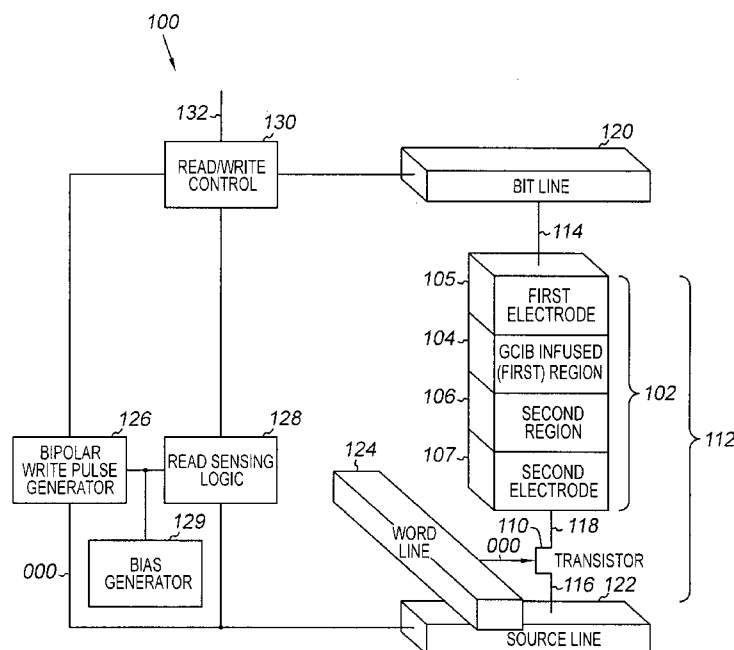


Fig. 1

(57) Abstract: The present disclosure includes GCIB-treated resistive devices, devices utilizing GCIB-treated resistive devices (e.g., as switches, memory cells), and methods for forming the GCIB-treated resistive devices. One method of forming a GCIB-treated resistive device includes forming a lower electrode, and forming an oxide material on the lower electrode. The oxide material is exposed to a gas cluster ion beam (GCIB) until a change in resistance of a first portion of the oxide material relative to the resistance of a second portion of the oxide material. An upper electrode is formed on the first portion.



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